

## 2SK1341

### Silicon N Channel MOS FET

REJ03G0938-0200  
(Previous: ADE-208-1278)  
Rev.2.00  
Sep 07, 2005

#### Application

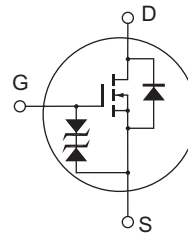
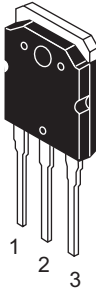
High speed power switching

#### Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

#### Outline

RENESAS Package code: PRSS0004ZE-A  
(Package name: TO-3P)



1. Gate
2. Drain  
(Flange)
3. Source

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	900	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	6	A
Drain peak current	I <sub>D(pulse)</sub> <sup>*1</sup>	15	A
Body to drain diode reverse drain current	I <sub>DR</sub>	6	A
Channel dissipation	P <sub>ch</sub> <sup>*2</sup>	100	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%  
 2. Value at T<sub>C</sub> = 25°C

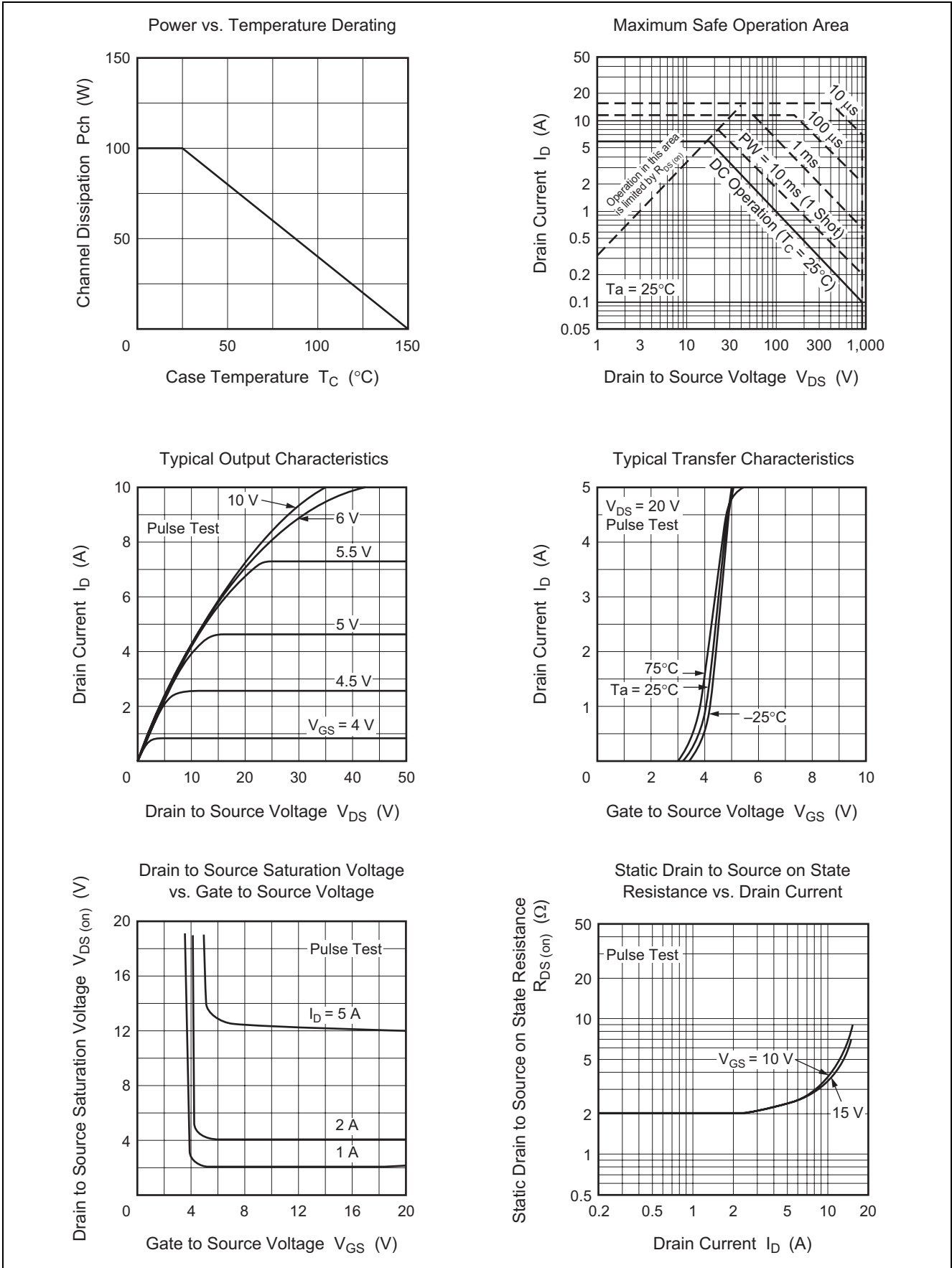
## Electrical Characteristics

(Ta = 25°C)

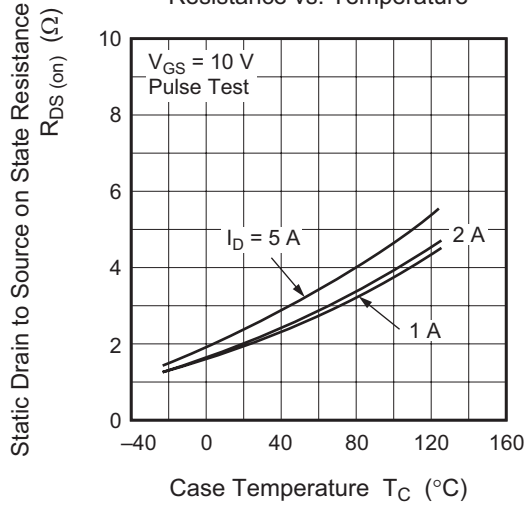
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	900	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±30	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	250	μA	V <sub>DS</sub> = 720 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	2.0	—	3.0	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Static drain to source on state resistance	R <sub>DS(on)</sub>	—	2.0	3.0	Ω	I <sub>D</sub> = 3 A, V <sub>GS</sub> = 10 V <sup>*3</sup>
Forward transfer admittance	y <sub>fs</sub>	2.3	3.7	—	S	I <sub>D</sub> = 3 A, V <sub>DS</sub> = 20 V <sup>*3</sup>
Input capacitance	C <sub>iss</sub>	—	980	—	pF	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0, f = 1 MHz
Output capacitance	C <sub>oss</sub>	—	400	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	195	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	20	—	ns	I <sub>D</sub> = 3 A, V <sub>GS</sub> = 10 V, R <sub>L</sub> = 10 Ω
Rise time	t <sub>r</sub>	—	80	—	ns	
Turn-off delay time	t <sub>d(off)</sub>	—	125	—	ns	
Fall time	t <sub>f</sub>	—	100	—	ns	
Body to drain diode forward voltage	V <sub>DF</sub>	—	0.9	—	V	I <sub>F</sub> = 6 A, V <sub>GS</sub> = 0
Body to drain diode reverse recovery time	t <sub>rr</sub>	—	1000	—	ns	I <sub>F</sub> = 6 A, V <sub>GS</sub> = 0, di <sub>F</sub> /dt = 100 A/μs

Note: 3. Pulse test

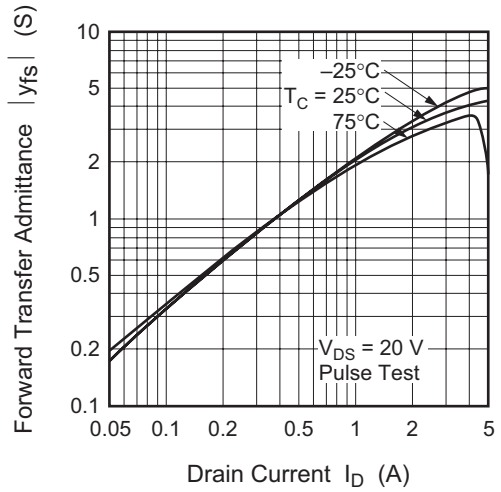
查询 Characteristic 供应商



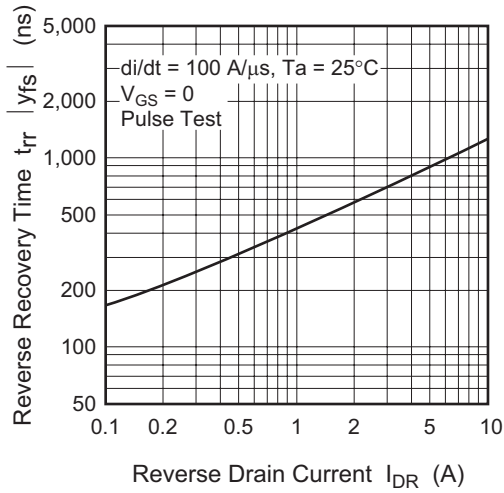
查询"2SK1341-5"供应商 **Static Drain to Source on State Resistance vs. Temperature**



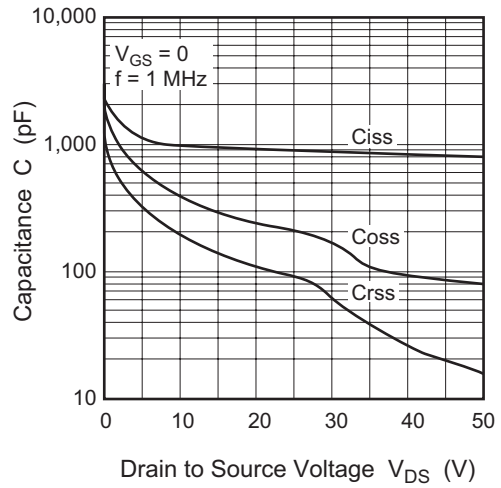
**Forward Transfer Admittance vs. Drain Current**



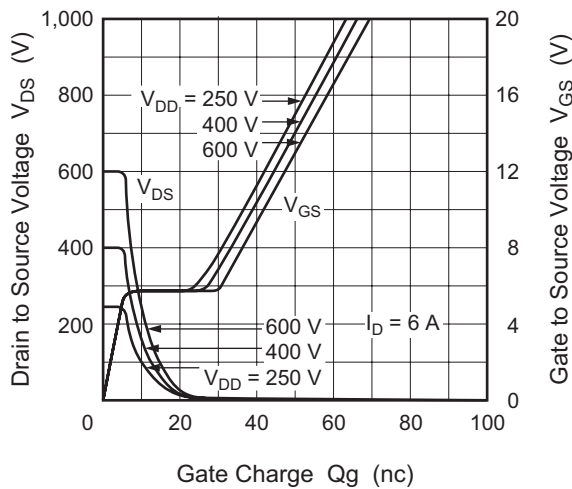
**Body to Drain Diode Reverse Recovery Time**



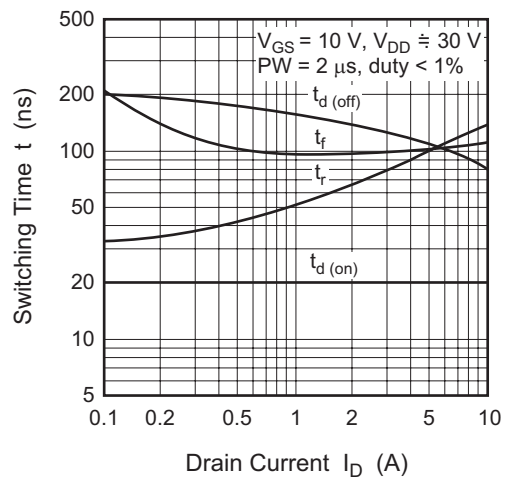
**Typical Capacitance vs. Drain to Source Voltage**



**Dynamic Input Characteristics**

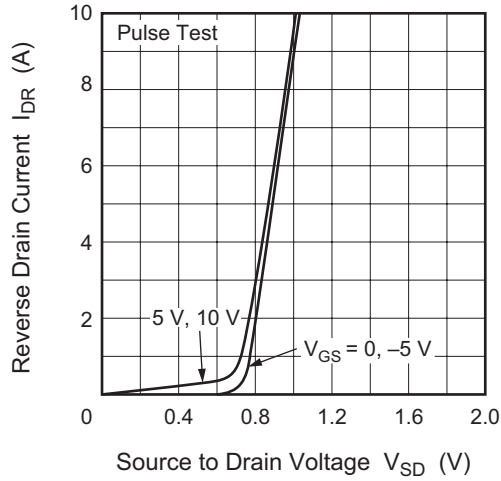


**Switching Characteristics**

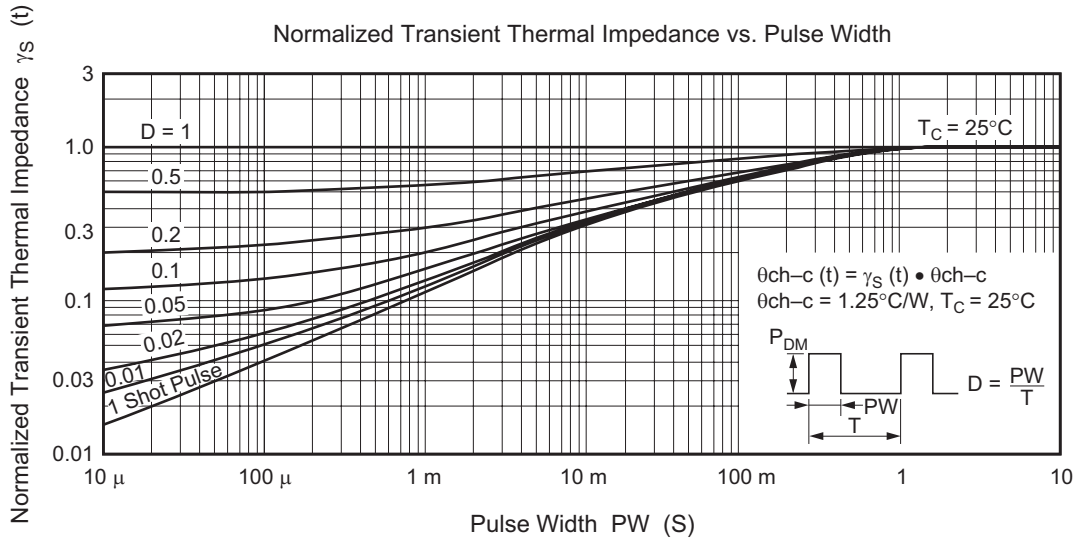


[查询"2SK1341-E"供应商](#)

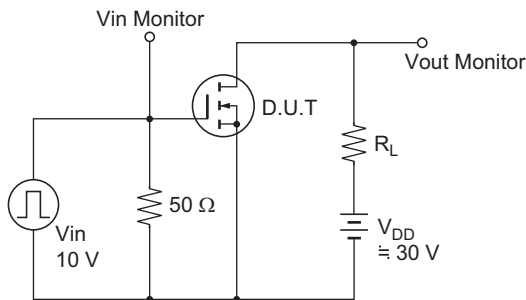
Reverse Drain Current vs. Source to Drain Voltage



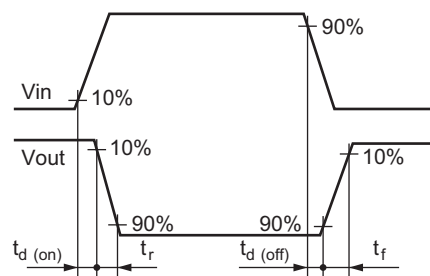
Normalized Transient Thermal Impedance vs. Pulse Width



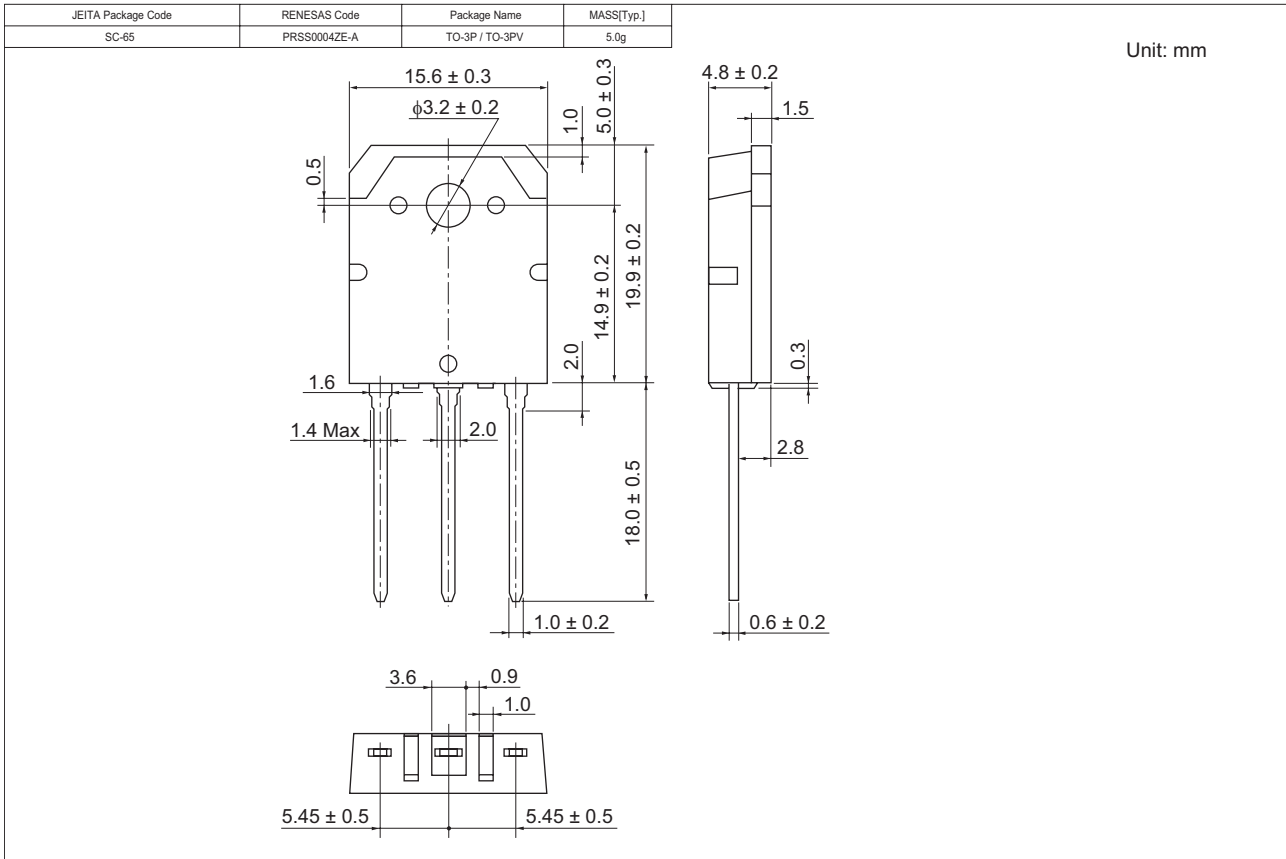
Switching Time Test Circuit



Waveforms



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK1341-E	500 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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